



# PJM10H40NTF

## N-Channel Enhancement Mode Power MOSFET

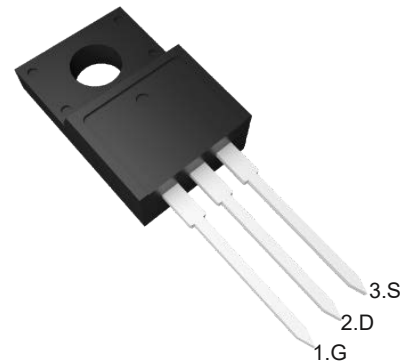
### Features

- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation
- Low gate charge and low  $R_{DS(on)}$
- $V_{DS} = 100V, I_D = 40A$   
 $R_{DS(on)} < 17m\Omega @ V_{GS} = 10V$

### Applications

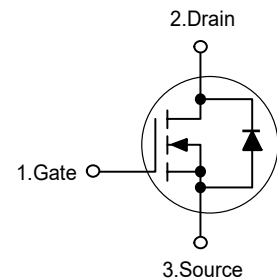
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

### TO-220F



1.Gate 2.Drain 3.Source

### Schematic diagram



### Absolute Maximum Ratings

Ratings at 25°C case temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	40	A
Drain Current-Pulsed <sup>Note1</sup>	$I_{DM}$	160	A
Single pulse avalanche energy <sup>Note4</sup>	$E_{AS}$	520	mJ
Maximum Power Dissipation	$P_D$	100	W
Junction Temperature	$T_J$	175	°C
Storage Temperature Range	$T_{STG}$	-55 to +175	°C

### Thermal Characteristics

Maximum Junction-to-Case <sup>Note2</sup>	$R_{\theta JC}$	0.783	°C/W
---	-----------------	-------	------



# PJM10H40NTF

## N-Channel Enhancement Mode Power MOSFET

### Electrical Characteristics

(T<sub>C</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100	--	--	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V	--	--	0.1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	--	--	±10	μA
Gate Threshold Voltage <sup>Note3</sup>	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	--	2.5	V
Drain-Source On-Resistance <sup>Note3</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	--	14	17	mΩ
Forward Transconductance <sup>Note3</sup>	g <sub>FS</sub>	V <sub>DS</sub> =25V, I <sub>D</sub> =28A	32	--	--	S
<b>Dynamic Characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz	--	1133	--	pF
Output Capacitance	C <sub>oss</sub>		--	70	--	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		--	71	--	pF
<b>Switching Characteristics</b>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =30V, R <sub>L</sub> =15Ω I <sub>D</sub> =2A, V <sub>GS</sub> =10V, R <sub>G</sub> =2.5Ω	--	5	--	nS
Turn-on Rise Time	t <sub>r</sub>		--	4	--	nS
Turn-off Delay Time	t <sub>d(off)</sub>		--	16	--	nS
Turn-off Fall Time	t <sub>f</sub>		--	5	--	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DD</sub> =30V, I <sub>D</sub> =30A, V <sub>GS</sub> =10V	--	23	--	nC
Gate-Source Charge	Q <sub>gs</sub>		--	5	--	nC
Gate-Drain Charge	Q <sub>gd</sub>		--	6.5	--	nC
<b>Source-Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>Note3</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =28A	--	--	1.2	V
Diode Forward Current <sup>Note2</sup>	I <sub>S</sub>		--	--	40	A

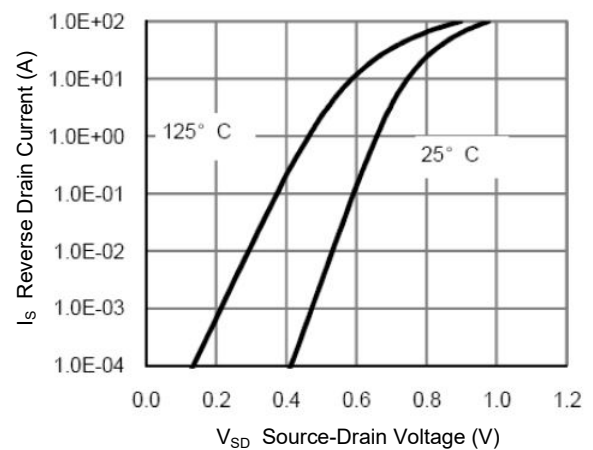
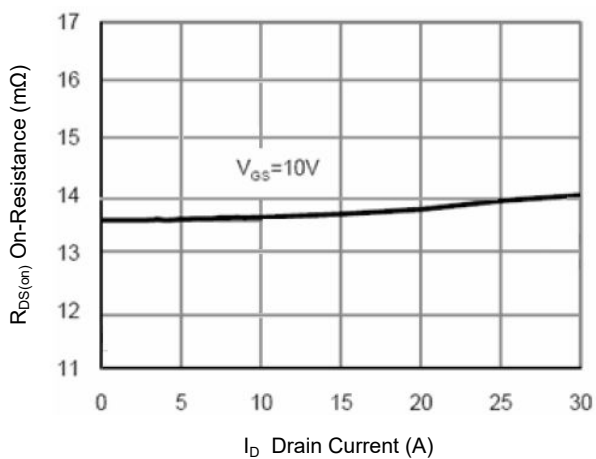
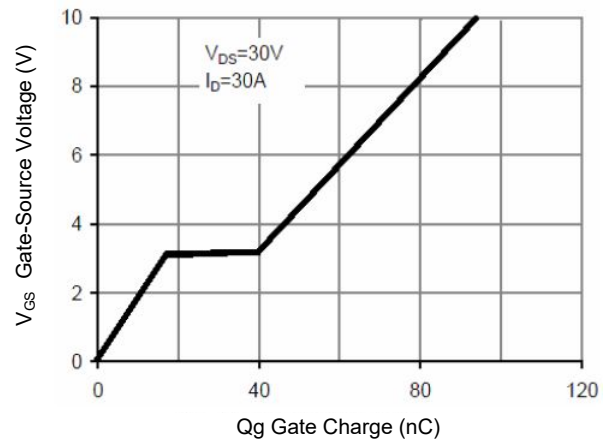
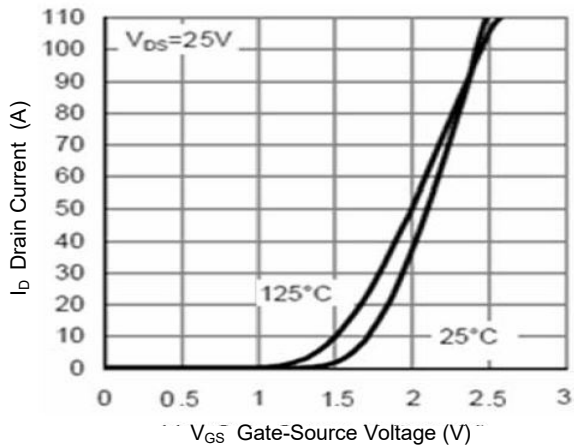
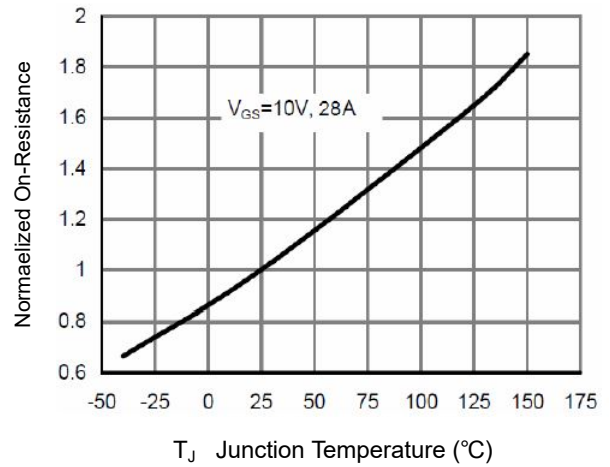
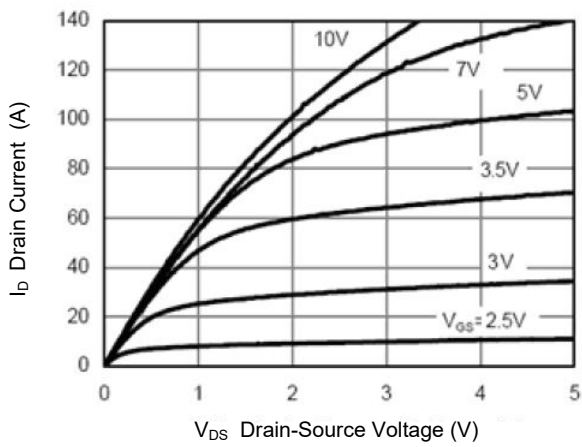
- Note: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.  
 2. Surface Mounted on FR4 Board, t ≤ 10 sec.  
 3. Pulse Test: Pulse width ≤ 300μs, duty cycle ≤ 2%.  
 4. E<sub>AS</sub> Condition: V<sub>DD</sub>=50V, V<sub>GS</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω, Start T<sub>J</sub>=25°C.



# PJM10H40NTF

## N-Channel Enhancement Mode Power MOSFET

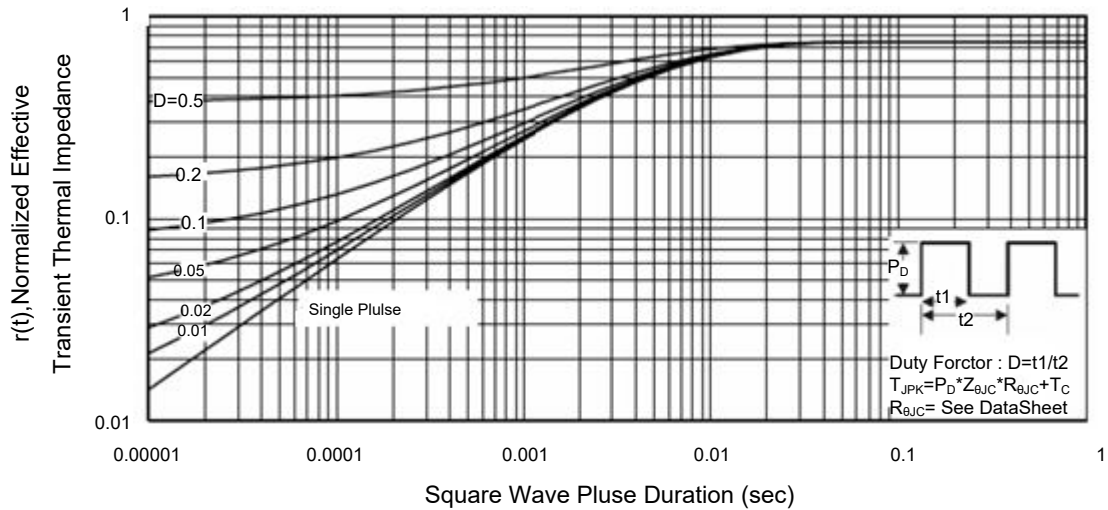
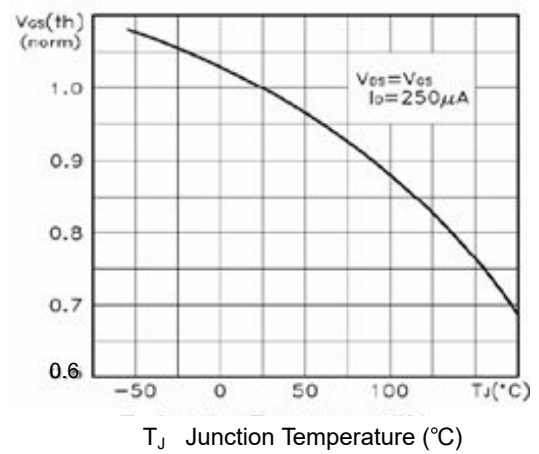
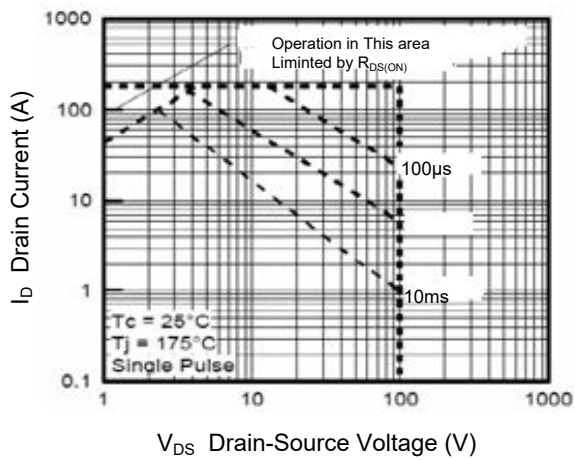
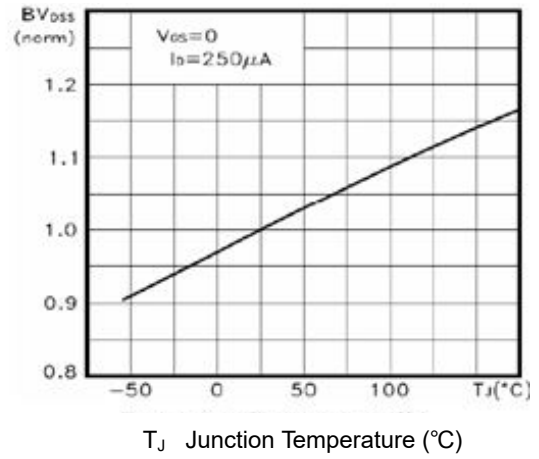
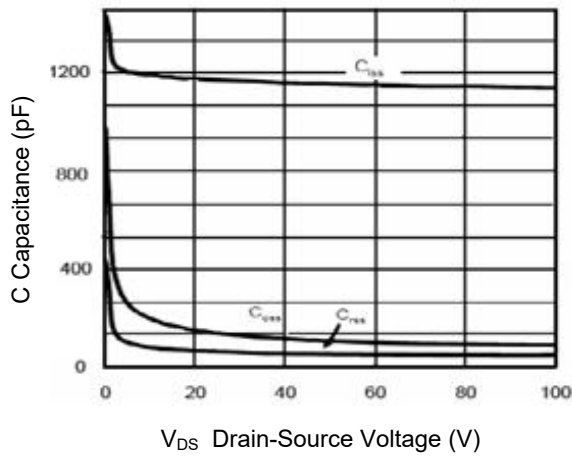
### Typical Characteristic Curves





# PJM10H40NTF

## N-Channel Enhancement Mode Power MOSFET





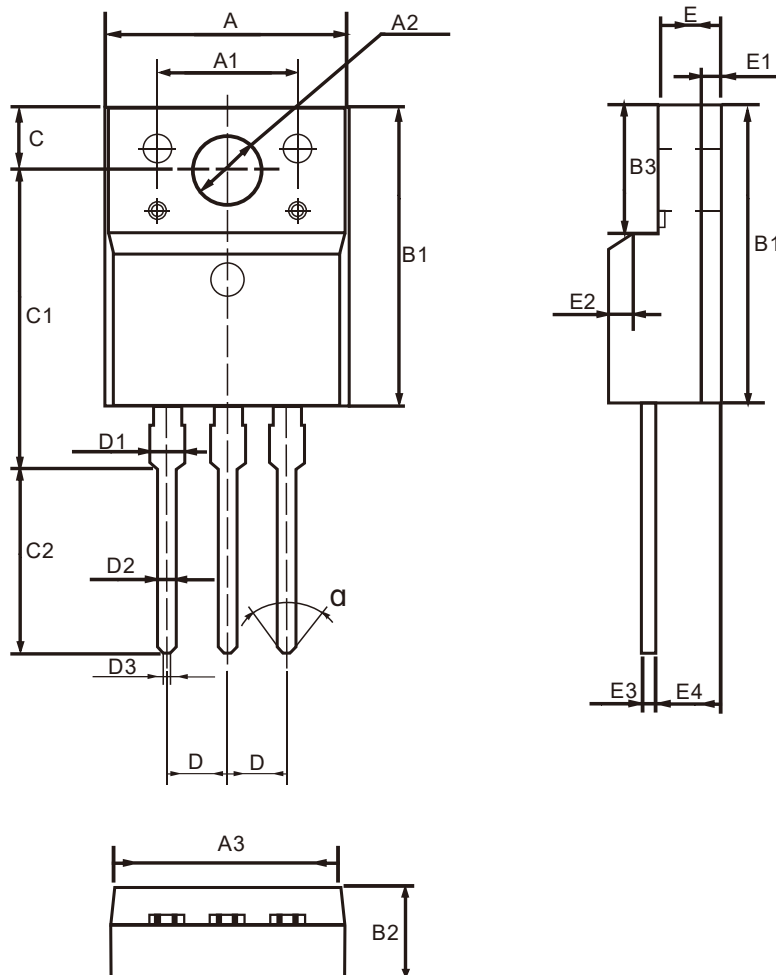
# PJM10H40NTF

## N-Channel Enhancement Mode Power MOSFET

### Package Outline

TO-220F

Dimensions in mm



TO-220F Package Dimensions

UNIT: mm

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	9.80		10.60	D		2.54	
A1		7.00		D1	1.15		1.55
A2	2.90		3.40	D2	0.60		1.00
A3	9.10		9.90	D3	0.20		0.50
B1	15.40		16.40	E	2.24		2.84
B2	4.35		4.95	E1		0.70	
B3	6.00		7.40	E2		1.0×45°	
C	3.00		3.70	E3	0.35		0.65
C1	15.00		17.00	E4	2.30		3.30
C2	8.80		10.80	α (度)		30°	